

AMENDMENTS TO THE CLAIMS

1. (Currently amended) A method for manufacturing a substrate with a plasma processing system, the method comprising:

obtaining a component of a plasma processing system which has been coated with a film of material;

disposing said component in a first plasma processing chamber; ~~said component having been coated outside of said plasma processing chamber;~~

disposing a substrate on a chuck in the first plasma processing chamber; ~~and~~

forming a first plasma in a processing region within the first plasma processing chamber; wherein the film of material has been coated using a second plasma in a second plasma processing chamber different from said first plasma processing chamber; and

wherein the chemistries of the first and second plasmas are substantially the same.

2. (Original) The method for manufacturing a substrate with a plasma processing system as recited in claim 1, wherein the obtaining includes obtaining a component from one of a component manufacturer and plasma processing chamber manufacturer.

3.-4. (Cancelled)

5. (Currently amended) The method for manufacturing a substrate with a plasma processing system as recited in claim 1[[4]], wherein the second plasma processing chamber used to coat the component is similar to the first plasma processing chamber where the substrate is disposed.

6. (Original) The method for manufacturing a substrate with a plasma processing system as recited in claim 1, wherein the film of material comprises a minimum thickness determined by at least one of a customer specification, a supplier specification, a process recipe, a chamber parameter, a pre-seasoning time, and a type of process used to manufacture the substrate.

7. (Original) The method for manufacturing a substrate with a plasma processing system as recited in claim 1, wherein the film of material comprises a uniformity determined by at least one of a customer specification, a supplier specification, a process recipe, a chamber parameter, a pre-seasoning time, and a type of process used to manufacture the substrate.

8. (Currently amended) The method for manufacturing a substrate with a plasma processing system as recited in claim 1, wherein the film of material comprises a material that is determined by at least one of a customer specification, a supplier specification, a process recipe, a chamber parameter, a pre-seasoning time, and type of process used to manufacture the substrate.

9. (Original) The method for manufacturing a substrate with a plasma processing system as recited in claim 1, wherein the film of material has a thickness within a range of about 1 to about 500 microns.

10. (Cancelled)

11. (Original) The method for manufacturing a substrate with a plasma processing system as recited in claim 1, further comprising pumping excess gas through a pump opening arranged in the plasma processing chamber.

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12. (Original) The method for manufacturing a substrate with a plasma processing system as recited in claim 11, wherein:

the obtaining includes obtaining a pumping deposition shield that has been coated with a film of material; and

the component disposing includes disposing said pumping deposition shield in the pump opening.

13.-31. (Withdrawn)